SQJ150EP

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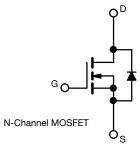
Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0084
I _D (A)	66
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET[®] Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





FREE

ABSOLUTE MAXIMUM RATINGS	6 (T _C = 25 °C, unless	otherwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	40	V	
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current	T _C = 25 °C	L.	66		
Continuous drain current	T _C = 125 °C	I _D	38		
Continuous source current (diode conduction)		I _S	58	А	
Pulsed drain current ^a		I _{DM}	168		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	22		
Single pulse avalanche energy		E _{AS}	24.2	mJ	
Maximum power dissipation ^a	T _C = 25 °C	PD	65	W	
	T _C = 125 °C	гD	22	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) c			260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^b	R _{thJA}	68	°C/W
Junction-to-case (drain)		R _{thJC}	2.3	0/10

Notes

b. When mounted on 1" square PCB (FR4 material)

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static	•						
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		40	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	2.5	3.0	3.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA
		V _{GS} = 0 V V _{DS} = 40 V		-	-	1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 15 A	-	0.0068	0.0084	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 15 A, T _J = 125 °C	-	-	0.0128	Ω
		$V_{GS} = 10 V$	I _D = 15 A, T _J = 175 °C	-	-	0.0152	
Forward transconductance b	9 _{fs}	V _{DS}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 10 \text{ A}$			-	S
Dynamic ^b	•	•		•		•	
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	910	1274	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	362	508	pF
Reverse transfer capacitance	C _{rss}			-	43	60	
Total gate charge ^c	Qg			-	15	20	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	-	4.9	-	nC
Gate-drain charge c	Q _{gd}			-	3.5	-	
Gate resistance	Rg	f = 1 MHz		1.9	4.2	6.7	Ω
Turn-on delay time ^c	t _{d(on)}				18	24	- ns
Rise time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 20 \text{ V}, \ R_{\text{L}} = 0.5 \ \Omega \\ I_{\text{D}} \cong 40 \text{ A}, \ V_{\text{GEN}} = 10 \text{ V}, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	17	21	
Turn-off delay time ^c	t _{d(off)}			-	35	44	
Fall time ^c	t _f			-	13	17	
Source-Drain Diode Ratings and Char	acteristics ^b	•		•		•	
Pulsed current ^a	I _{SM}			-	-	168	Α
Forward voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V		-	-	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 6 A, di/dt = 100 A/μs		-	25	36	ns
Body diode reverse recovery charge	Q _{rr}			-	10	14	nC
Reverse recovery fall time	t _a			-	10	14	
Reverse recovery rise time	t _b			-	15	21	ns
Body diode peak reverse recovery current	I _{RM(REC)}		-	0.8	1.1	A	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

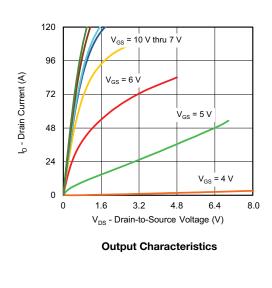
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

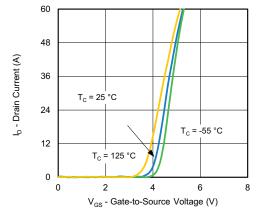
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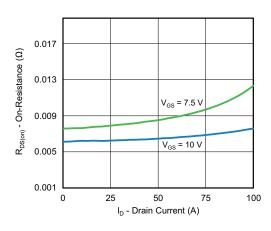
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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

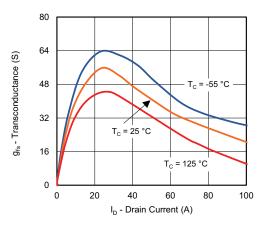




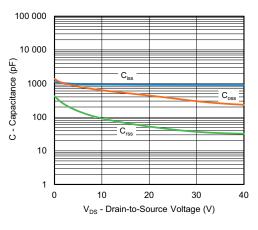
Transfer Characteristics



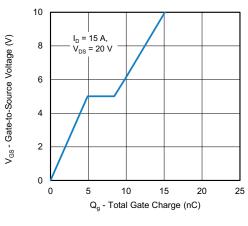
On-Resistance vs. Drain Current



Transconductance



Capacitance



Gate Charge

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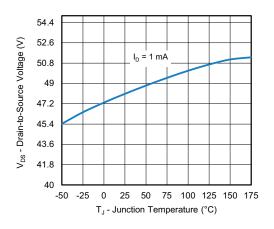
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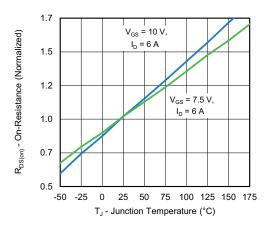
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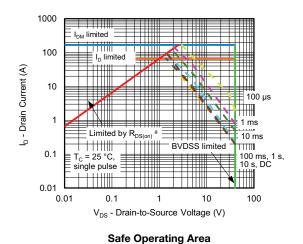
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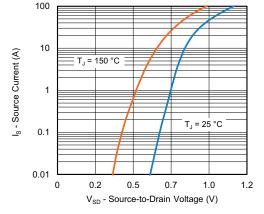


Drain Source Breakdown vs. Junction Temperature

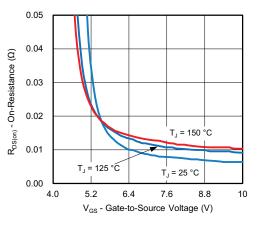


On-Resistance vs. Junction Temperature

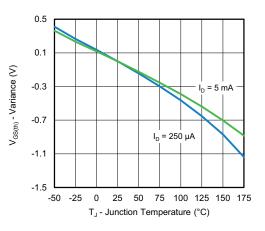




Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to Source Voltage



Variance vs. Junction Temperature

Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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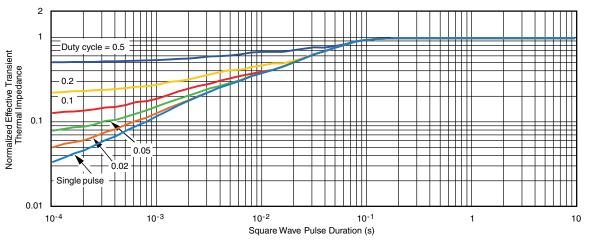
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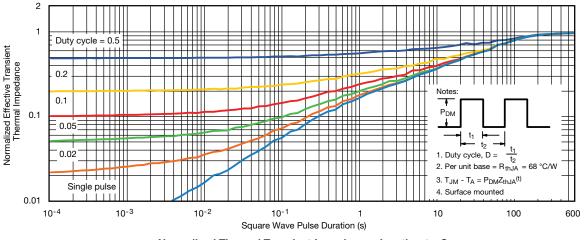
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

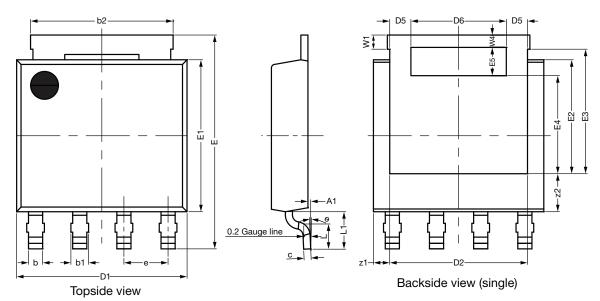
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PowerPAK[®] SO-8L (PPKSO8LWLA) Case Outline 3



DIM.		MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX		
А	1.00	1.05	1.10	0.039	0.041	0.043		
A1	0.00		0.127	0.000		0.005		
b	0.33	0.41	0.49	0.013	0.016	0.019		
b1	0.43	0.51	0.59	0.017	0.020	0.023		
b2	4.00	4.10	4.20	0.157	0.161	0.165		
С	0.15	0.20	0.25	0.006	0.008	0.010		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D5	0.51	0.61	0.71	0.020	0.024	0.028		
D6	2.64	2.74	2.84	0.104	0.108	0.112		
е		1.27 BSC		0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	3.18	3.28	3.38	0.125	0.129	0.133		
E3	3.48	3.58	3.68	0.137	0.141	0.145		
E4	2.72	2.82	2.92	0.107	0.111	0.115		
E5	0.71	0.81	0.91	0.028	0.032	0.036		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
W1	0.31	0.41	0.51	0.012	0.016	0.020		
W4	0.31	0.36	0.41	0.012	0.014	0.016		
z1	0.37	0.47	0.57	0.015	0.019	0.022		
z2	0.99	1.09	1.19	0.039	0.043	0.047		
θ	0°		5°	0°		5°		

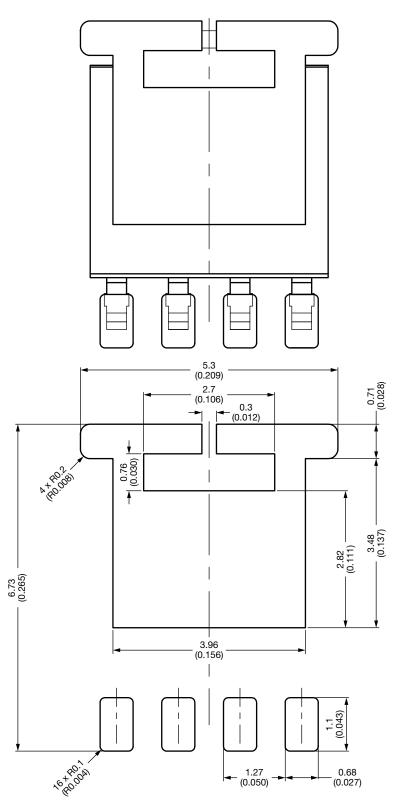
Note

• Millimeter will govern



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Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)

Revision: 24-Aug-2021

Document Number: 78020



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